

# 제23회 한국반도체학술대회

2016년 2월 22일(월)-24일(수), 강원도 하이원리조트

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## E. Compound Semiconductors 분과

Room K

청옥Ⅱ+Ⅲ(6층)

2016년 2월 24일(수) 08:30-10:00

[WK1-E] GaN Power Device

좌장 : 문재경(한국전자통신연구원), 장태훈(전북대학교)

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| WK1-E-2 | 08:45-09:00 | <b>Improvement of Off-state Performance of AlGaIn/GaN HFET with TMAH Surface Treatment</b><br>Won-Sang Park, Do-Kywn Kim, Dong-Hyeok Son, Ryun-Hwi Kim, Jun-Hyeok Lee, Quan Dai, Dae-Hyun Kim, In Man Kang, and Jung-Hee Lee<br><i>School of Electrical Engineering, Kyungpook National University</i>   |
| WK1-E-3 | 09:00-09:15 | <b>Study on Temperature Dependent Dynamic On-resistance and Switching Loss of Clamped AlGaIn/GaN MOS-HFETs</b><br>Sang-Woo Han, Sung-Hoon Park, Hyun-Seop Kim, and Ho-Young Cha<br><i>School of Electronic and Electrical Engineering, Hongik University</i>   |
| WK1-E-4 | 09:15-09:30 | <b>Improvement of Output Power Performance in AlGaIn/GaN HFETs with Multi-level Metallization</b><br>SeungKyu Oh <sup>1</sup> , Taehoon Jang <sup>2</sup> , In Yeol Hong <sup>1</sup> , Gil Jun Lee <sup>1</sup> , and Joon Seop Kwak <sup>1</sup><br><sup>1</sup> <i>Department of Printed Electronics Engineering, Sunchon National University,</i> <sup>2</sup> <i>Semiconductor Physics Research Center, Department of Semiconductor Science and Technology, Chonbuk National University</i> |
| WK1-E-5 | 09:30-09:45 | <b>Suppressed Charge Trapping Behaviors of ALD HfAlO<sub>x</sub> GaN MOS Device with Sulfur Passivation</b><br>Hoonhee Han, Donghwan Lim, Youngjin Kim, and Changhwan Choi<br><i>Division of Materials Science and Engineering, Hanyang University</i>   |
| WK1-E-6 | 09:45:10:00 | <b>AlGaIn/GaN-on-Si Device with Monolithic Gate Driver</b><br>Sung-Hoon Park, Sang-Woo Han, Hyun-Seop Kim, and Ho-Young Cha<br><i>School of Electrical and Electronic Engineering, Hongik University</i>   |